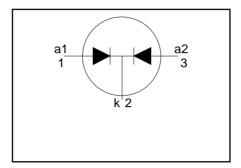
BYV72EF series

FEATURES

- Low forward volt drop
- Fast switching
- Soft recovery characteristic
- Reverse surge capability
- High thermal cycling performance
- · Isolated mounting tab

SYMBOL



QUICK REFERENCE DATA

$$V_{R} = 150 \text{ V}/ 200 \text{ V}$$

$$V_{F} \le 0.9 \text{ V}$$

$$I_{O(AV)} = 20 \text{ A}$$

$$I_{RRM} = 0.2 \text{ A}$$

$$t_{rr} \le 28 \text{ ns}$$

GENERAL DESCRIPTION

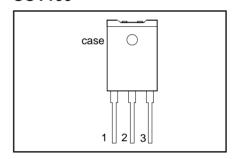
Dual, ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYV72EF series is supplied in the conventional leaded SOT199 package.

PINNING

PIN	DESCRIPTION	
1	anode 1 (a)	
2	cathode (k)	
3	anode 2 (a)	
tab	isolated	

SOT199



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	N. MAX.		UNIT
V _{RRM} V _{RWM} V _R	Peak repetitive reverse voltage Crest working reverse voltage Continuous reverse voltage	$\textbf{BYV72EF}$ $T_{hs} \leq 125^{\circ}\text{C}$	-	-150 150 150 150	-200 200 200 200	V
I _{O(AV)}	Average rectified output current (both diodes conducting) ¹	square wave δ = 0.5; T _{hs} ≤ 78 °C	-	2	0	A
I _{FRM}	Repetitive peak forward current per diode Non-repetitive peak forward current per diode	$t = 25 \mu s$; $\delta = 0.5$; $T_{hs} \le 78 ^{\circ}C$ t = 10 ms t = 8.3 ms sinusoidal; with reapplied	- - -	15	0 50 60	A A A
I _{RRM}	Repetitive peak reverse current per diode		-	0	.2	А
T _{stg}	Non-repetitive peak reverse current per diode Storage temperature Operating junction temperature	$t_p = 100 \ \mu s$	- -40 -		.2 50 50	, C , C

¹ Neglecting switching and reverse current losses.

BYV72EF series

ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _C	Electrostatic discharge capacitor voltage	Human body model; C = 250 pF; R = 1.5 kΩ	1	8	kV

ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. ≤ 65 % ; clean and dustfree	1	ı	2500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	22	-	pF

THERMAL RESISTANCES

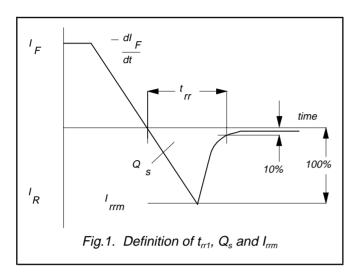
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink	both diodes conducting with heatsink compound without heatsink compound per diode	-		4.0 8.0	K/W K/W
R_{thj-a}	Thermal resistance junction to ambient	with heatsink compound without heatsink compound in free air	- - -	- - 35	5.0 9.0 -	K/W K/W K/W

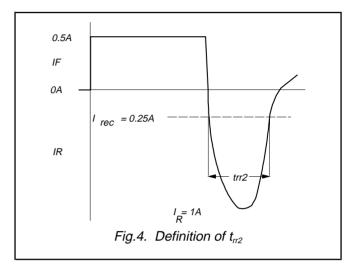
ELECTRICAL CHARACTERISTICS

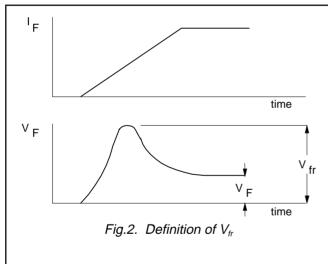
characteristics are per diode at T_j = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage	$I_F = 15 \text{ A}; T_i = 150^{\circ}\text{C}$	-	0.83	0.90	V
		I _F = 15 A	-	0.95	1.05	V
		$I_{\rm F} = 30 \text{ A}$	-	1.00	1.20	V
l _R	Reverse current	$\dot{V}_R = V_{RWM}$; $T_j = 100 ^{\circ}C$	-	0.5	1	mΑ
		$V_R = V_{RWM}$	-	10	100	μΑ
$Q_{\rm s}$	Reverse recovery charge	$V_R = V_{RWM}$ $I_F = 2 \text{ A}; V_R \ge 30 \text{ V}; -dI_F/dt = 20 \text{ A/}\mu\text{s}$	-	6	15	'nC
t _{rr1}	Reverse recovery time	$ I_{\rm F} = 1 \text{ A}; V_{\rm R} \ge 30 \text{ V};$	-	20	28	ns
	_	-dI _F /dt = 100 A/μs				
t _{rr2}	Reverse recovery time	$I_F = 0.5 \text{ A to } I_R = 1 \text{ A}; I_{rec} = 0.25 \text{ A}$	-	13	22	ns
V _{fr}	Forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A/µs}$	-	1	-	V

BYV72EF series







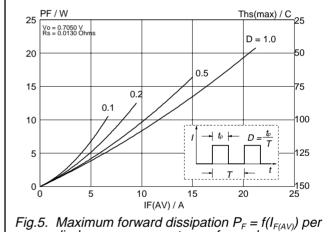
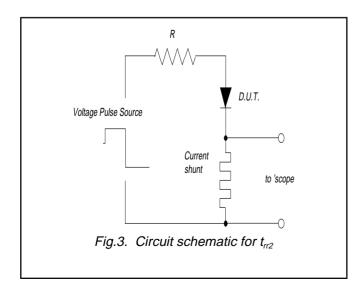


Fig.5. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.



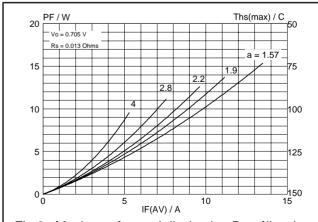
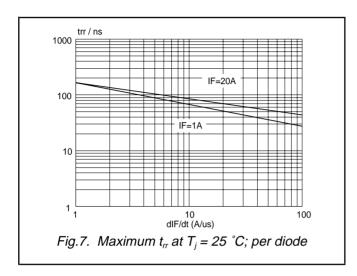
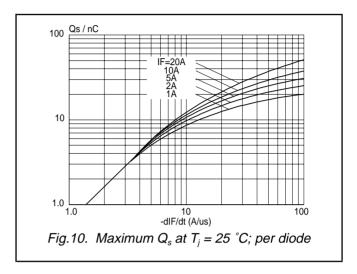
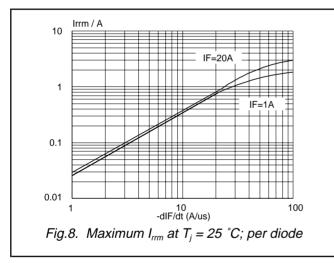


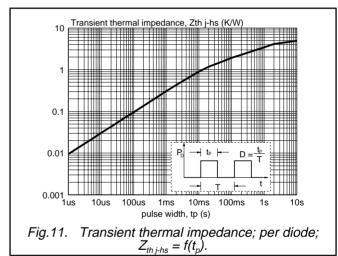
Fig.6. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = form factor $= I_{F(RMS)} / I_{F(AV)}$.

BYV72EF series









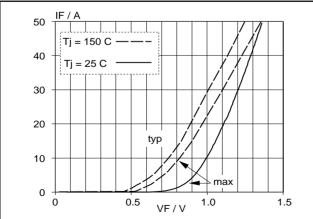
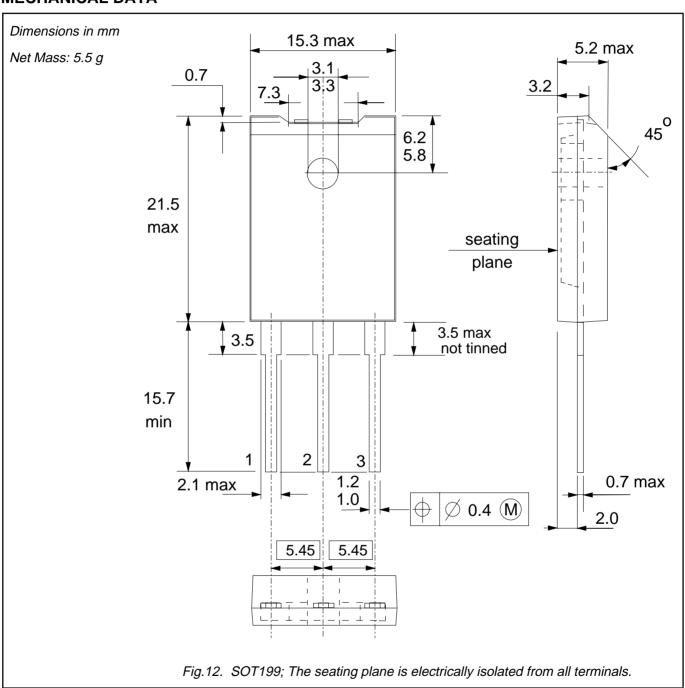


Fig.9. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_j

BYV72EF series

MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for F-pack envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier diodes ultrafast, rugged

BYV72EF series

DEFINITIONS

Data sheet status				
Objective specification This data sheet contains target or goal specifications for product development.				
Preliminary specification This data sheet contains preliminary data; supplementary data may be published later.				
Product specification This data sheet contains final product specifications.				
Limiting values				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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